

AlGaAs Laser Diode

Description

The SLD104AU is a AlGaAs laser diode developed for positive power supplies. In comparison with the SLD104U, this device attains even lower power consumption levels.

Features

- Low power consumption
- Single power supply
- Low noise
- Microminiaturized package ($\phi 5.6\text{mm}$)

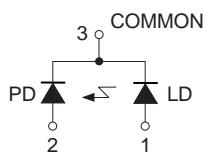
Structure

- AlGaAs double hetero-type laser diode
- PIN photo diode for laser optical power output monitor

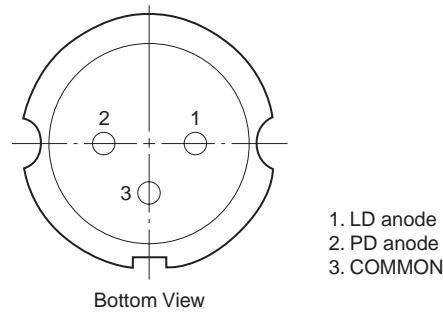
Absolute Maximum Ratings ($T_c = 25^\circ\text{C}$)

• Optical power output	Po	5	mW	
• Reverse voltage	V _R	LD	2	V
	PD		15	V
• Operating temperature	T _{opr}	-10 to +60	°C	
• Storage temperature	T _{stg}	-40 to +85	°C	

Connection Diagram



Pin Configuration



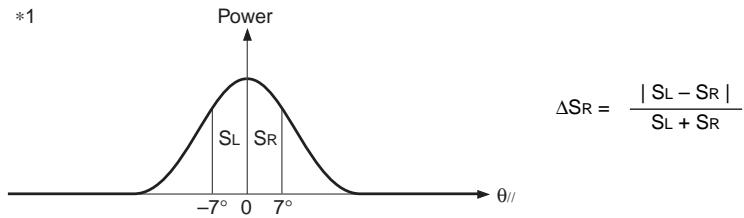
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Electrical and Optical Characteristics ($T_c = 25^\circ\text{C}$)

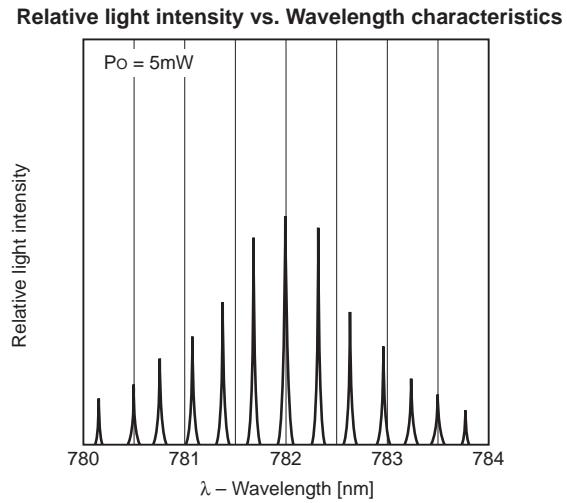
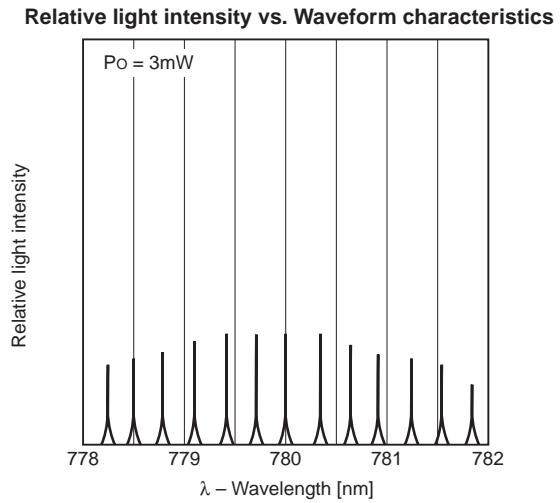
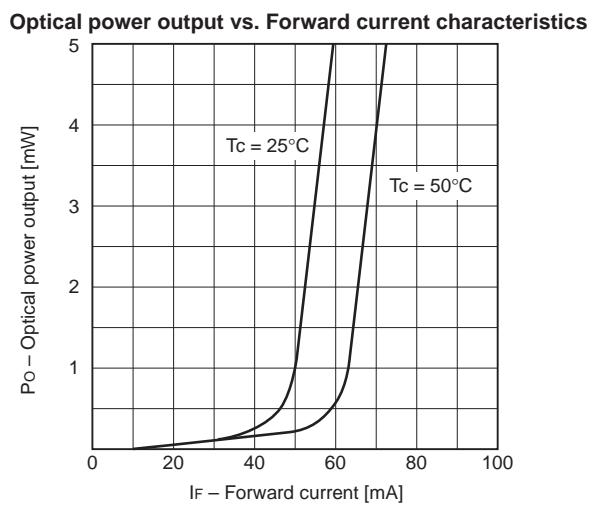
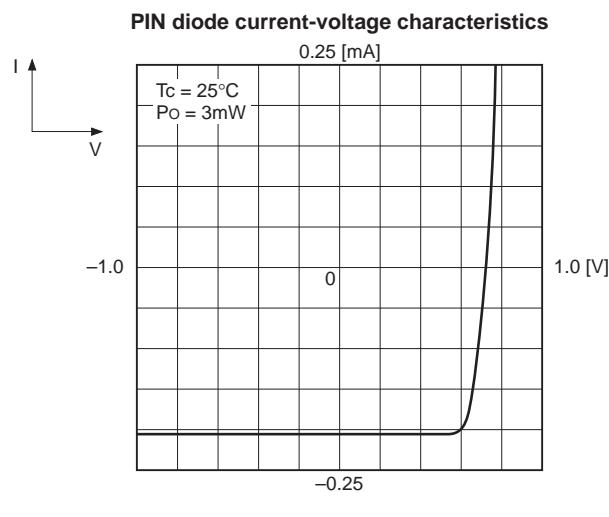
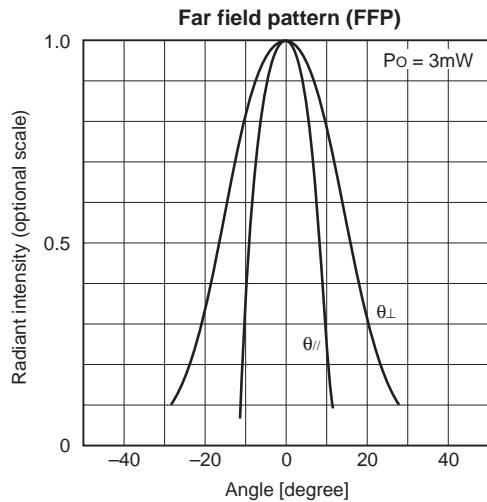
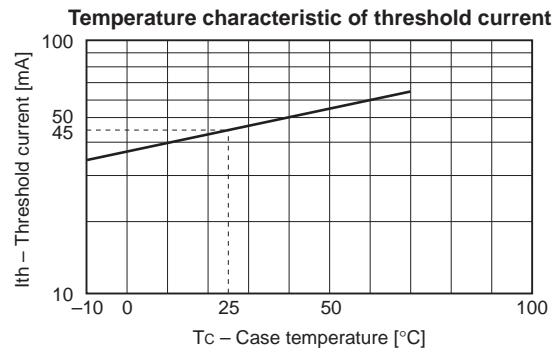
Tc: Case temperature

Item	Symbol	Condition	Min.	Typ.	Max.	Unit
Threshold current	I_{th}			45	60	mA
Operating current	I_{op}	$P_o = 3\text{mW}$		52	70	mA
Operating voltage	V_{op}	$P_o = 3\text{mW}$	1.7	1.9	2.5	V
Wavelength	λ	$P_o = 3\text{mW}$	760	780	800	nm
Monitor current	I_m	$P_o = 3\text{mW}, V_R = 5\text{V}$	0.08	0.15	0.4	mA
Radiation angle (F. W. H. M.*)	Perpendicular	$\theta \perp$	$P_o = 3\text{mW}$	20	32	45 degree
	Parallel	$\theta \parallel$		9	17	25 degree
	Asymmetry	ΔS_R^{*1}			20	%
Positional accuracy	Position	$\Delta X, \Delta Y, \Delta Z$	$P_o = 3\text{mW}$		± 150	μm
	Angle	$\Delta \phi \perp$			± 3	degree
Differential efficiency	η_D	$P_o = 3\text{mW}$	0.2	0.45	0.7	mW/mA
Astigmatism	A_s	$P_o = 3\text{mW}$ $ Z \parallel -Z \perp $			15	μm
Signal to noise ratio	S/N	$f_c = 7.5\text{MHz}$ $\Delta f = 30\text{kHz}$ $P_o = 4\text{mW}$		88		dB
Dark current of PD	I_D	$V_R = 5\text{V}$			150	nA
Capacitance of PD	C_T	$V_R = 5\text{V}, f = 1\text{MHz}$			30	pF

* F. W. H. M. : Full Width at Half Maximum

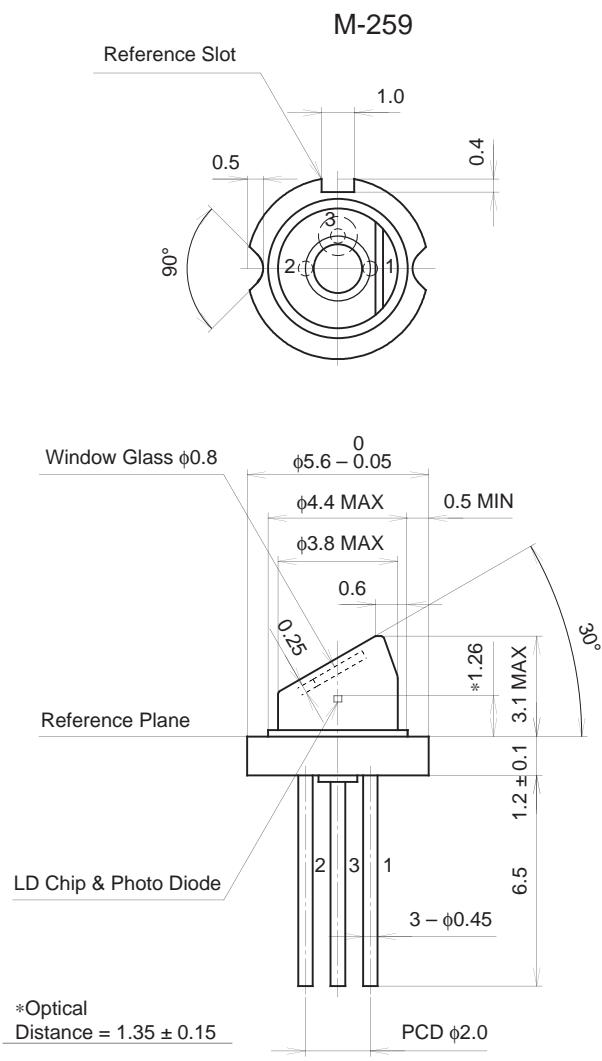


Example of Representative Characteristics



Package Outline

Unit: mm



SONY CODE	M-259
EIAJ CODE	_____
JEDEC CODE	_____

PACKAGE WEIGHT	0.3g
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